

1. Description

The ESDA6V1-5SC6 is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium.

2. Features

- IEC 61000-4-2 Level 4 ESD Protection
 - ± 12 kV Contact Discharge
 - ± 17 kV Air Discharge
- 60W Peak pulse Power (8/20us)
- Low clamping voltage
- Working voltage: 5V
- Low leakage current
- RoHS compliant
- Protecting 4 unidirectional lines
- Ultra-low capacitance: 0.6pF Typ.

3. Applications

- USB 2.0
- Monitors and flat panel displays
- 10/100/1000 ethernet
- Notebook computers
- SIM ports
- ATM interface

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ESDA6V1-5SC6	SOT-23-6L	.V05	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

Table-1 Ordering information

5. Pin Configuration and Functions

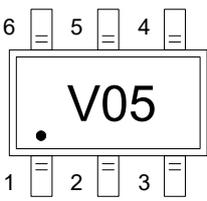
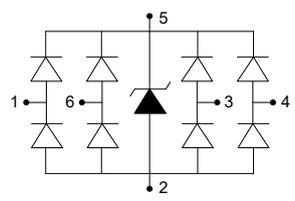
Pin	Name	Description	Outline	Circuit Diagram
1	IO1	Connect to I/O		
2	GND	Connect to GND		
3	IO2	Connect to I/O		
4	IO3	Connect to I/O		
5	Vcc	Connect to Vcc		
6	IO4	Connect to I/O		

Table-2 Pin configuration

6. Specification

6.1. Absolute Maximum rating

Over operating free-air temperature range (unless otherwise noted)

Parameters	Symbol	Min.	Max.	Unit
Peak pulse power (tp=8/20us)@25°C	P _{pk}	-	60	W
Peak pulse current (tp=8/20us)@25°C	I _{PP}	-	4.5	A
ESD (IEC61000-4-2 air discharge) @25°C	V _{ESD}	-	±17	kV
ESD (IEC61000-4-2 contact discharge) @25°C	V _{ESD}	-	±12	kV
Junction temperature	T _J	-	150	°C
Operating temperature	T _{OP}	-40	125	°C
Storage temperature	T _{STG}	-55	150	°C
Lead temperature	T _L	-	260	°C

Table-3 Absolute Maximum rating

6.2. Electrical Characteristics

At TA = 25°C unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	6.0			V
Reverse Leakage Current	I_R	$V_{RWM}=5V$			1.0	μA
Clamping Voltage	V_C	$I_{PP}=1A$; $t_p=8/20\mu s$		9.0	11.0	V
Clamping Voltage	V_C	$I_{PP}=4.5A$; $t_p=8/20\mu s$		12.0	15.0	V
Junction Capacitance	C_J	I/O to GND; $V_R=0V$; $f=1MHz$		0.6	1.0	pF
		Between I/O; $V_R=0V$; $f=1MHz$		0.3	0.5	pF

Table-4 Electrical Characteristics

Symbol	Parameters
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
I_F	Forward Current
V_F	Forward Voltage @ I_F

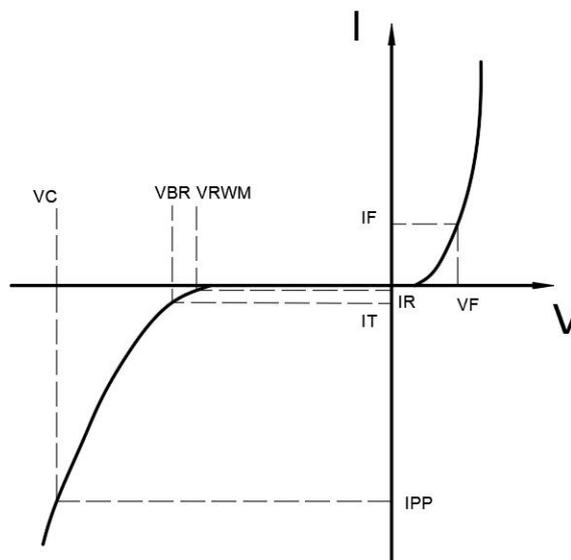


Figure1: Clamping Voltage vs. Peak Pulse Current

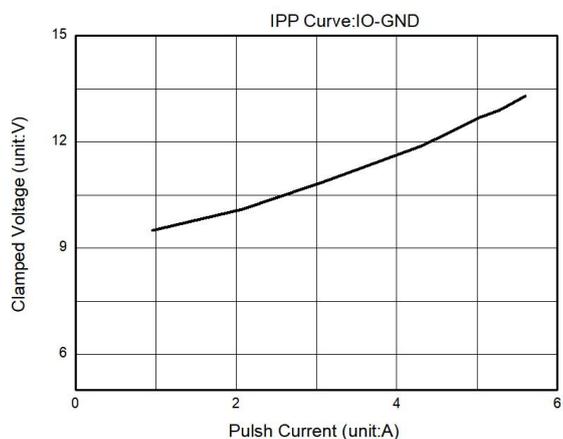


Figure2: 8 X 20us Pulse Waveform

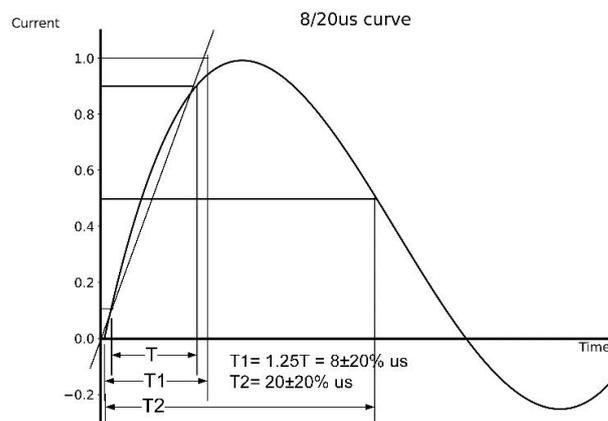


Figure3: Junction Capacitance vs, Reverse Voltage

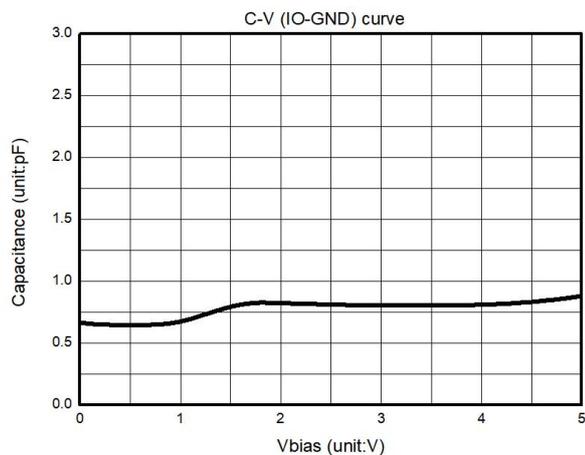


Figure4: Junction Capacitance vs, Reverse Voltage

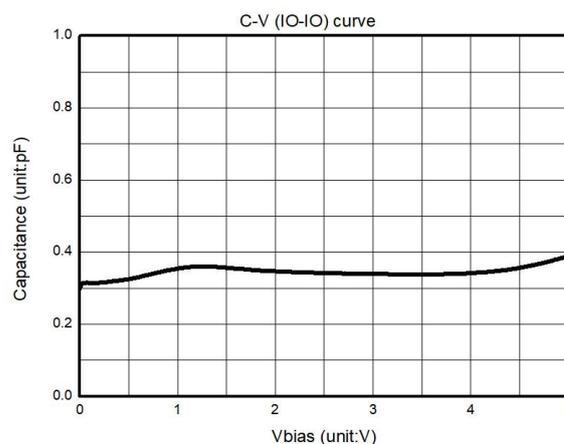
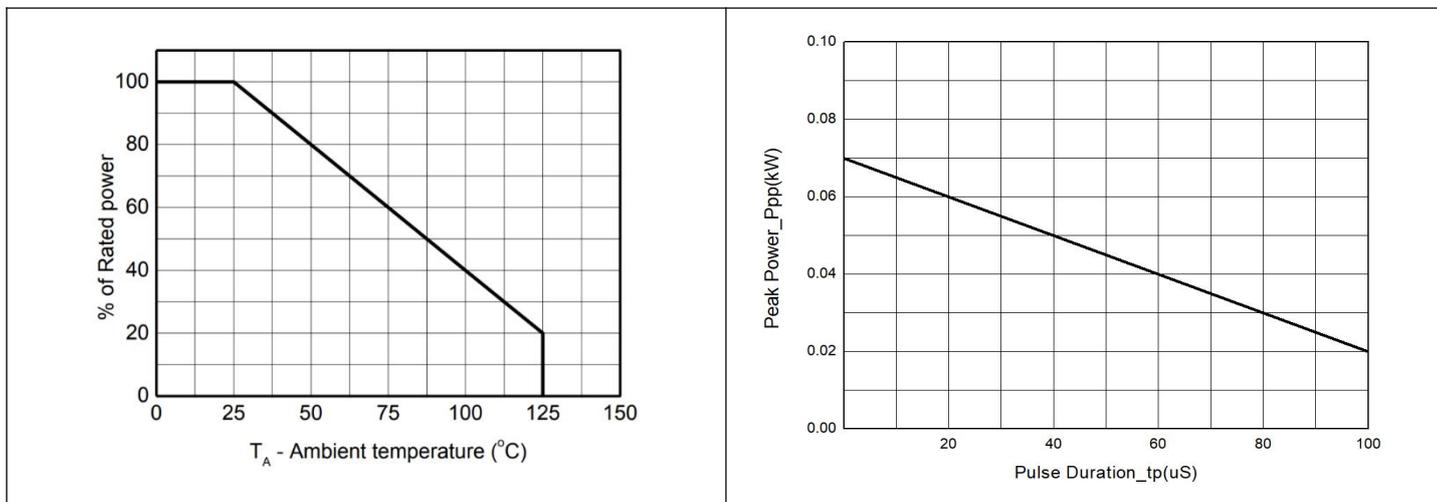


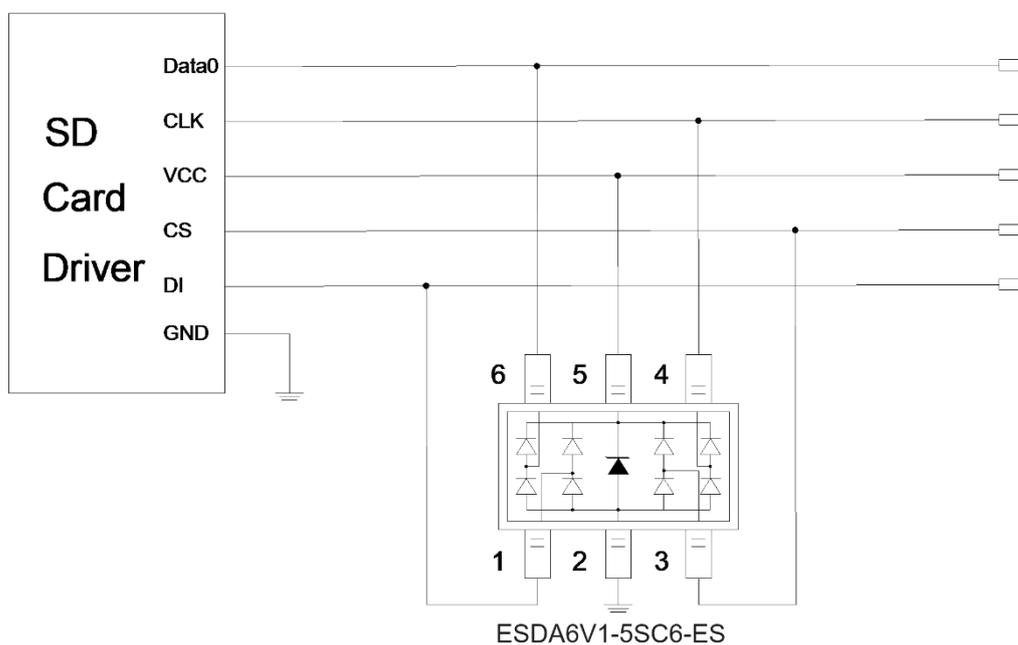
Figure5: Power derating vs. Ambient temperature

Figure6: Peak Pulse Power vs, Pulse Time



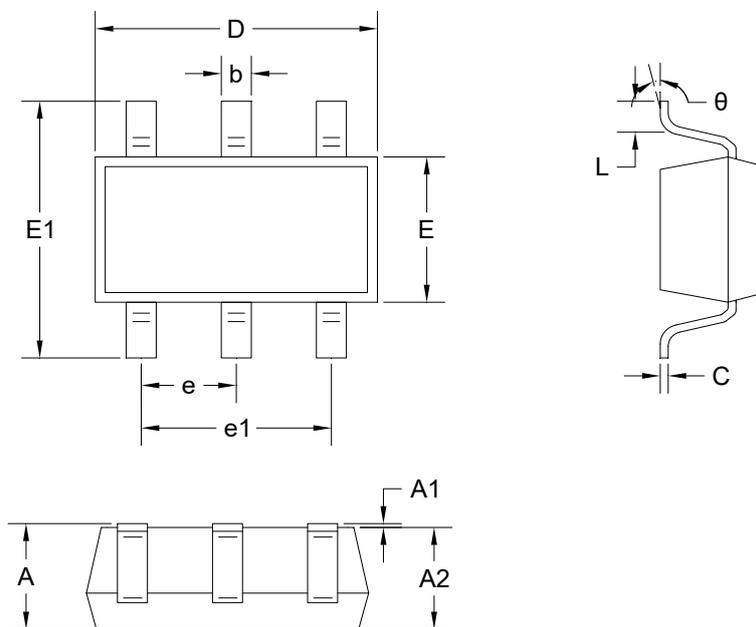
7. Typical Characteristic

8. Typical Application



Typical Interface Application

9. Dimension (SOT-23-6L)



Unit: mm

Symbol		A	A1	A2	b	c	D
Spec	Min	1.050	0.000	1.050	0.300	0.100	2.820
	Max	1.250	0.100	1.150	0.500	0.200	3.020
Symbol		E	E1	e	e1	L	θ
Spec	Min	1.500	2.650	0.950BSC	1.800	0.300	0°
	Max	1.700	2.950		2.000	0.600	8°

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C±5°C	5sec±1sec
Pb-Free device	260°C+0/-5°C	5sec±1sec



This integrated circuit can be damaged by ESD. BYSEMI Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.